

PATENT ABSTRACTS OF JAPAN

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(21)Application number : 2001-334170 (71)Applicant : MATSUSHITA ELECTRIC IND CO LTD

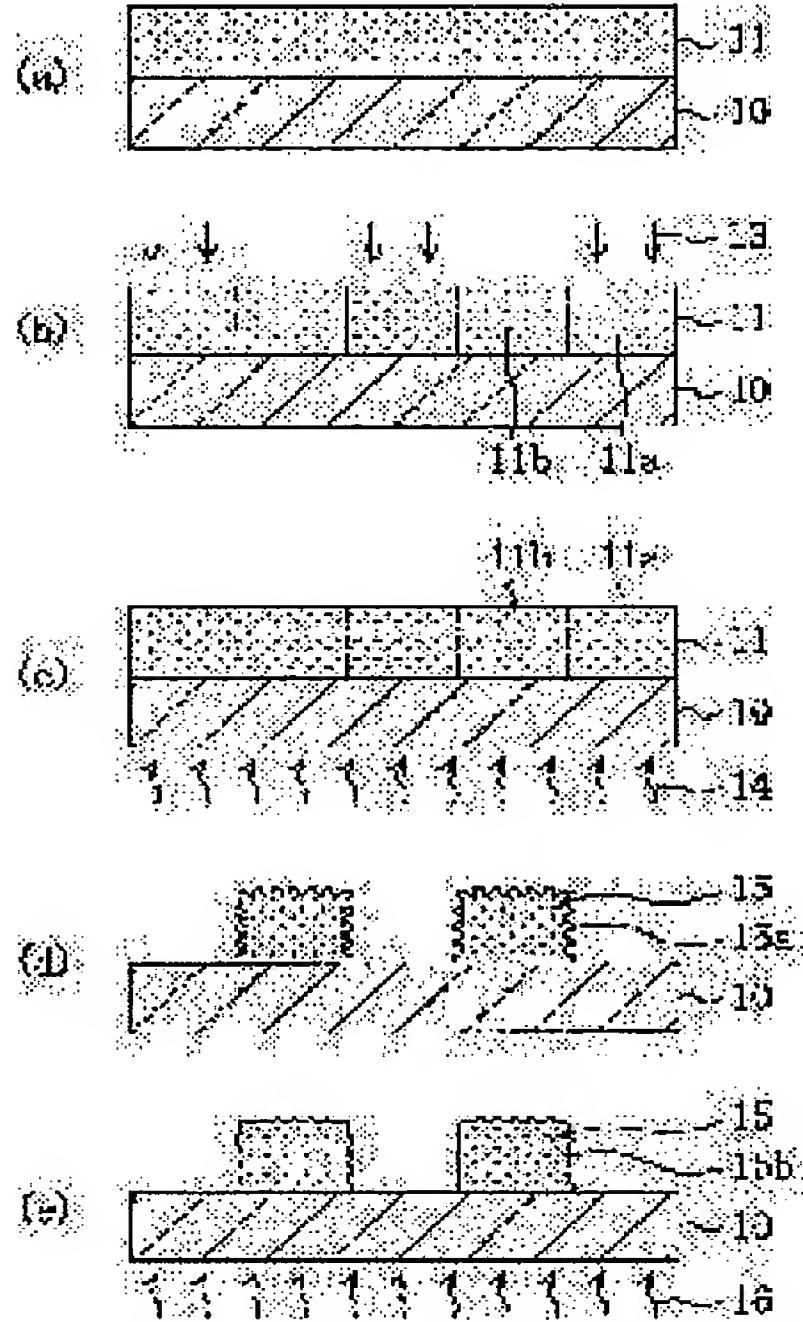
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(54) METHOD FOR FORMING PATTERN

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce dispersion in the size of a resist pattern.

SOLUTION: After a resist film 11 consisting of a chemically amplifying resist material containing a base polymer containing at least one ester of acrylate and methacrylate and an acid generating agent which generates acid by irradiation of light is formed, the resist film 11 is selectively irradiated with extreme UV rays 13 for pattern exposure. The resist film 11 subjected to the pattern exposure is developed to form a resist pattern 15 consisting of the non-exposed part of the resist film 11. The resist pattern 15 is heated to smoothen the roughness 15a of the pattern 15.



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